

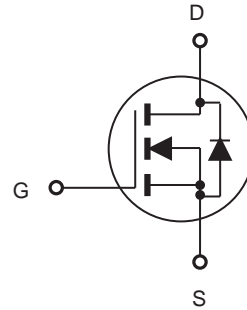
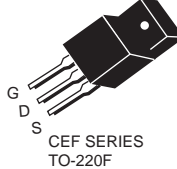
CEP02N6/CEB02N6 CEI02N6/CEF02N6

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP02N6	600V	5Ω	2A	10V
CEB02N6	600V	5Ω	2A	10V
CEI02N6	600V	5Ω	2A	10V
CEF02N6	600V	5Ω	2A ^e	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V _{DS}	600		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current-Continuous	I _D	2	2 ^e	A
Drain Current-Pulsed ^a	I _{DM} ^f	6	6 ^e	A
Maximum Power Dissipation @ T _C = 25°C - Derate above 25°C	P _D	60	29	W
		0.48	0.23	W/°C
Single Pulsed Avalanche Energy ^d	E _{AS}	125	125	mJ
Repetitive Avalanche Current ^a	I _{AR}	2	2	A
Repetitive Avalanche Energy ^a	E _{AR}	5.4	5.4	mJ
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	2.1	4.3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W

[查询"CEI02N6"供应商](#)



CEP02N6/CEB02N6 CEI02N6/CEF02N6

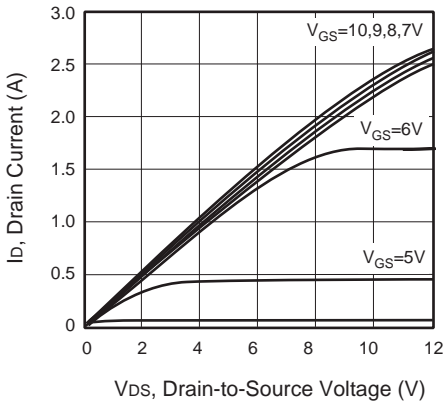


Figure 1. Output Characteristics

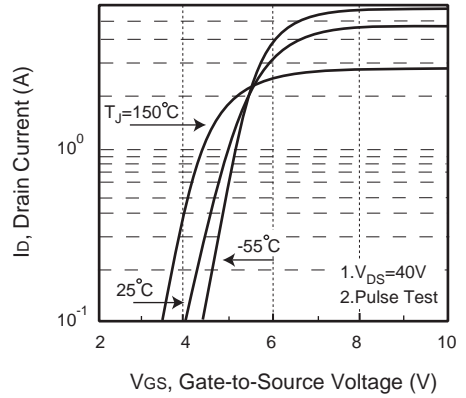


Figure 2. Transfer Characteristics

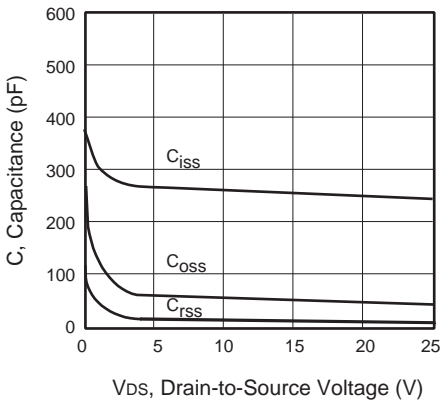


Figure 3. Capacitance

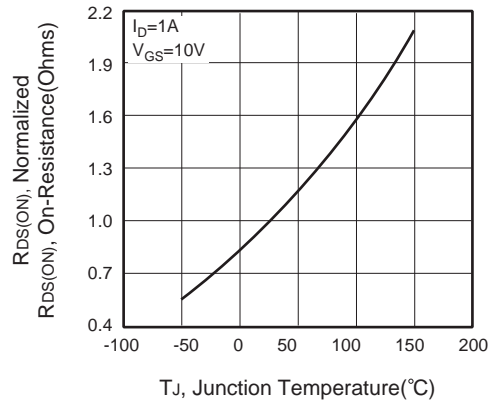


Figure 4. On-Resistance Variation with Temperature

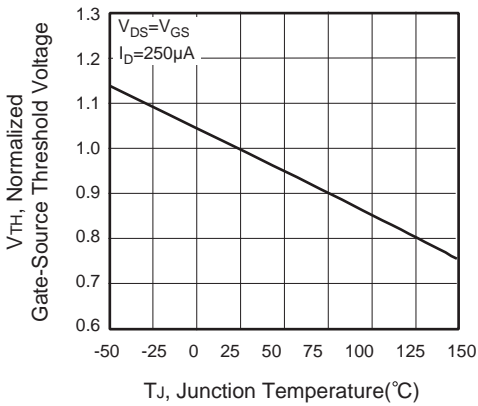


Figure 5. Gate Threshold Variation with Temperature

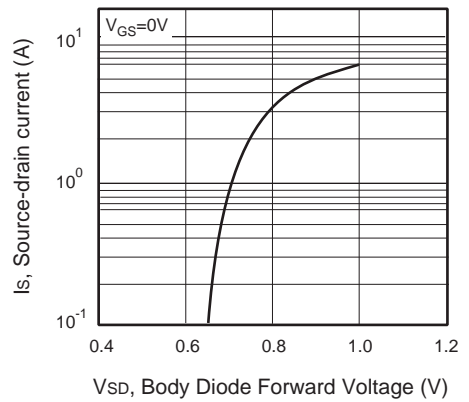
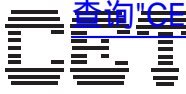


Figure 6. Body Diode Forward Voltage Variation with Source Current



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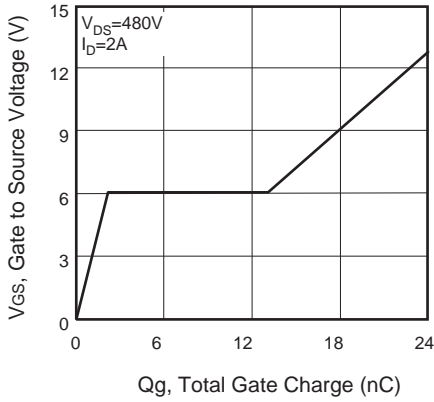


Figure 7. Gate Charge

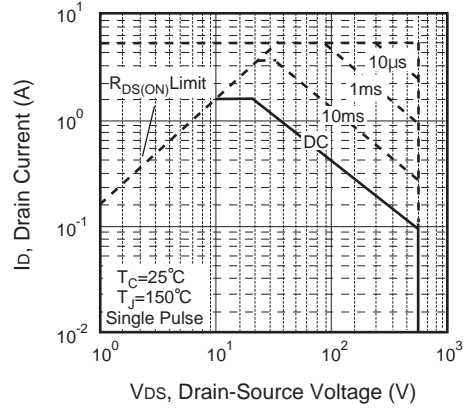


Figure 8. Maximum Safe Operating Area

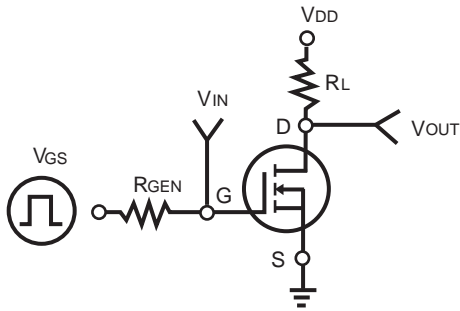


Figure 9. Switching Test Circuit

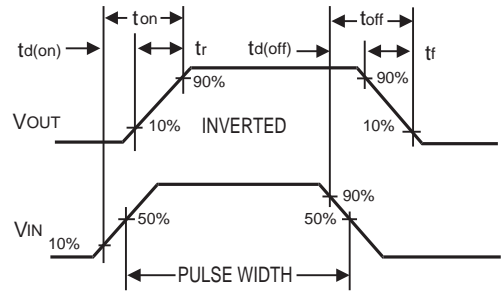


Figure 10. Switching Waveforms

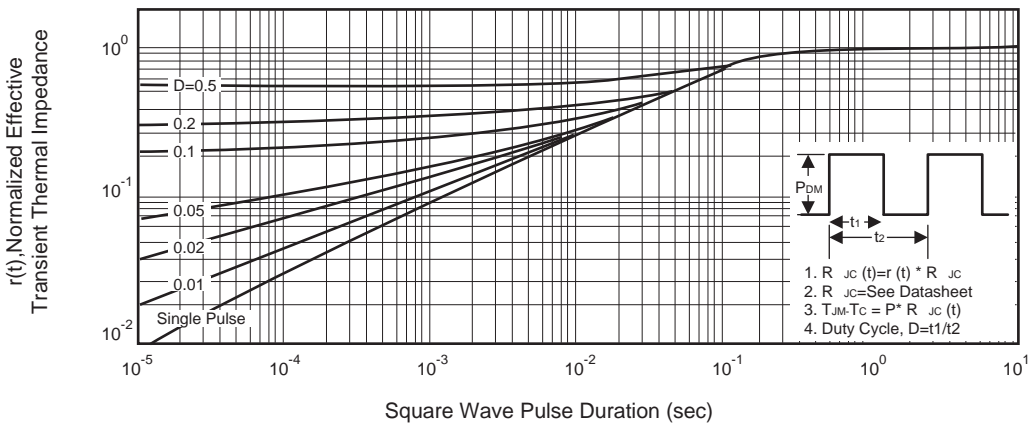


Figure 11. Normalized Thermal Transient Impedance Curve